	Application No.	Applicant(s)		
Notice of Allowability	10/776,191	MA ET AL.		
	Examiner	Art Unit		
	Kevin M. Bernatz	1773		
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI-	ars on the cover sheet with to (OR REMAINS) CLOSED in this or other appropriate communice GHTS. This application is subjected and MPEP 1308.	he correspondence add s application. If not inclu- ation will be mailed in due	ded e course. <b>THIS</b>	
1. This communication is responsive to <u>amendment filed 9/8/0</u>	<u>06</u> .			
2. ☑ The allowed claim(s) is/are <u>1-20</u> .				
<ol> <li>Acknowledgment is made of a claim for foreign priority un a)</li></ol>	been received. been received in Application N	o	ation from the	
Applicant has THREE MONTHS FROM THE "MAILING DATE" on noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		eply complying with the re	equirements	
4. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give	tted. Note the attached EXAMII	NER'S AMENDMENT or claration is deficient.	NOTICE OF	
5. CORRECTED DRAWINGS ( as "replacement sheets") must	t be submitted.			
(a) ☐ including changes required by the Notice of Draftsperso		PTO-948) attached		
1)  hereto or 2)  to Paper No./Mail Date				
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date				
identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the			e back) of	
<ol> <li>DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT F</li> </ol>	sit of BIOLOGICAL MATERI FOR THE DEPOSIT OF BIOLO	AL must be submitted. GICAL MATERIAL.	Note the	
Attachment(s)				
1. ☐ Notice of References Cited (PTO-892)	5. Notice of Inform	view Summary (PTO-413),		
2. Notice of Draftperson's Patent Drawing Review (PTO-948)				
<ul> <li>Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date</li></ul>	Paper No./Mai 8), 7. ⊠ Examiner's Am	Paper No./Mail Date <u>20060914</u> . 7. ⊠ Examiner's Amendment/Comment		
	8. X Examiner's Sta	8. X Examiner's Statement of Reasons for Allowance		
	9. 🗌 Other	9.  Other		

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## Election/Restriction

1. Claims 9 – 13 and 20 are allowable. The restriction requirement set forth on December 20, 2005, has been reconsidered in view of the allowability of claims to the elected invention pursuant to MPEP § 821.04(a). The restriction requirement is hereby withdrawn as to any claim that requires all the limitations of an allowable claim. Claims 1 – 8 and 14 – 19, directed to inventions no longer withdrawn from consideration because the claim(s) requires all the limitations of an allowable claim.

In view of the above noted withdrawal of the restriction requirement, applicant is advised that if any claim presented in a continuation or divisional application is anticipated by, or includes all the limitations of, a claim that is allowable in the present application, such claim may be subject to provisional statutory and/or nonstatutory double patenting rejections over the claims of the instant application.

Once a restriction requirement is withdrawn, the provisions of 35 U.S.C. 121 are no longer applicable. See *In re Ziegler*, 443 F.2d 1211, 1215, 170 USPQ 129, 131-32 (CCPA 1971). See also MPEP § 804.01.

## Reasons for Allowance

- 1. The present claims are deemed allowable over the reference Ma et al. (U.S. Patent No. 6,613,422 B1) since the reference is commonly assigned and a terminal disclaimer has been filed to obviate the obviousness-type double patenting rejection.
- 2. The present claims are deemed allowable over the references of record since the references of record fail to disclose or render obvious a structure comprising a layer of

undoped tetrahedral amorphous carbon (ta-C) having a mass density of carbon atoms greater than about 2.5 gms/cm³ and formed on said ta-C layer, a layer of nitrogendoped tetrahedral amorphous carbon (ta-C:N) having a mass density of carbon atoms greater than 2.0 gms/cm³.

Regarding Ma et al., the Examiner concurs with applicants' arguments.

Regarding Fujimaki et al., the Examiner was relying upon an inherency position with regard to a comparative example (*Paragraph 0062*), since Fujimaki et al. desires the second layer (i.e. applicants' ta-C:N layer) to be formed of only carbon (*Paragraph 0005*). With regard to claims 14 – 19, the Examiner further notes that Fujimaki et al. fails to teach or render obvious controlling the ta-C:N layer to possess a mass density of carbon greater than 2.0 gms/cm<sup>3</sup>.

While Jairson et al. disclose forming a carbon layer, which *may* be a *ta*-C:N layer, on a layer of ta-C having a high carbon mass density, Jairson et al. fail to teach or render obvious the ability to form the ta-C:N layer such that it meets the claimed mass density limitation. Specifically, the Examiner notes that applicants have provided evidence that nitrogen-doped carbon layers formed by a sputtering process allegedly cannot achieve carbon mass densities above 2.0 (*see graph, not in an executed declaration format, submitted with response filed June 30, 2006*). Additional evidence exists in Ma et al. ('422 B1) Figure 2, which shows that only in a narrow range of nitrogen content can a carbon density of 2.0 or higher be achieved <u>by an ion beam deposition (IBD) process</u>. Finally, the Examiner notes that Figure 1 of the present application supports and summarizes these evidentiary teachings regarding the ability

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of the various processes to obtain ta-C:N films possessing high carbon mass densities, which is supported by the teaching in Fujimaki et al. ('496 A1) (i.e. the ability to achieve higher mass density via a filtered cathodic arc deposition (FCAD) process). However, the Examiner deems that Jairson et al. (232 B2) teaches away from using a FCAD process to deposit the second carbon containing layer, since Jairson et al. desires a low carbon mass density for the second film.

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As such, the Examiner deems that there is insufficient specificity in the prior art to teach or render obvious the combined use of a layer of undoped tetrahedral amorphous carbon (ta-C) having a mass density of carbon atoms greater than about 2.5 gms/cm<sup>3</sup>, and formed on said ta-C layer, a layer of nitrogen-doped tetrahedral amorphous carbon (ta-C:N) having a mass density of carbon atoms greater than 2.0 gms/cm<sup>3</sup>.

3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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## Conclusion

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kevin M. Bernatz whose telephone number is (571) 272-1505. The examiner can normally be reached on M-F, 9:00 AM - 6:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carol Chaney can be reached on (571) 272-1284. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

KMB September 14, 2006 Kevin M. Bernatz, PhD Primary Examiner